

PMEG3030BEP

3 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 27 October 2009

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 3 A
- Reverse voltage: V_R ≤ 30 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{F(AV)}$	average forward current	square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$				
		T _{amb} ≤ 70 °C	<u>[1]</u> _	-	3	Α
		T _{sp} ≤ 140 °C	-	-	3	А
V_R	reverse voltage		-	-	30	V
V_{F}	forward voltage	$I_F = 3 A$	-	400	450	mV
I _R	reverse current	$V_{R} = 30 \text{ V}$	-	55	150	μΑ

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. [4]
2	anode	1 2	1 🖊 2
		<u> </u>	sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG3030BEP	-	plastic surface-mounted package; 2 leads	SOD128

4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3030BEP	A6

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C	-	30	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz			
		T _{amb} ≤ 70 °C	<u>[1]</u> -	3	Α
		T _{sp} ≤ 140 °C	-	3	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] _	50	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] $T_i = 25$ °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]			
		[3]	-	200	K/W	
			<u>[4]</u> -	-	120	K/W
			<u>[5]</u> _	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- 6] Soldering point of cathode tab.

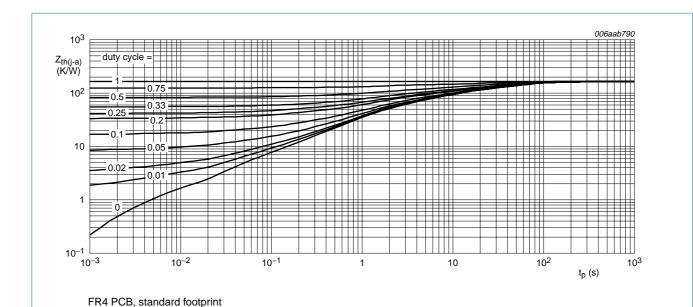


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

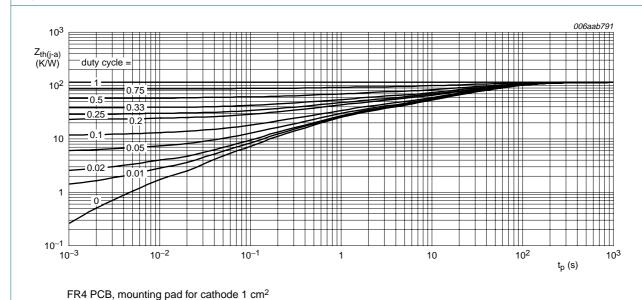
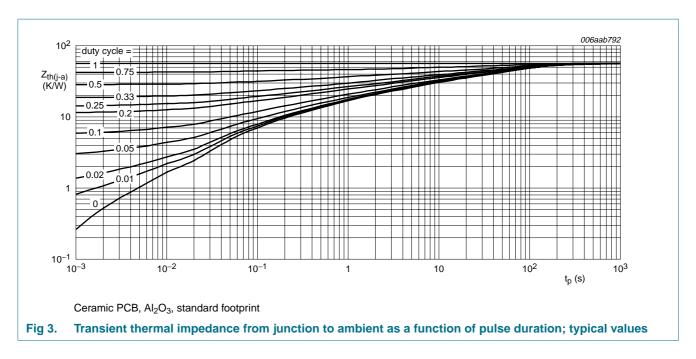


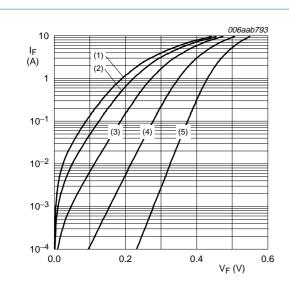
Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

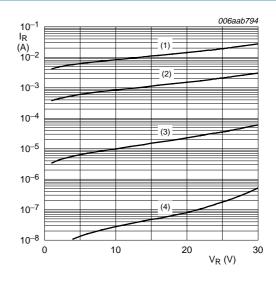
Table 7. Characteristics $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 0.1 A$	-	280	320	mV
		$I_F = 0.5 A$	-	330	380	mV
		I _F = 1 A	-	350	400	mV
		$I_F = 1.5 A$	-	365	420	mV
	I _F = 2 A	-	380	440	mV	
		$I_F = 3 A$	-	400	450	mV
I _R reverse current	reverse current	$V_R = 5 V$	-	6	-	μΑ
		V _R = 10 V	-	9	-	μΑ
	V _R = 30 V	-	55	150	μΑ	
C _d diode capacitance	f = 1 MHz					
		V _R = 1 V	-	500	-	pF
		V _R = 10 V	-	170	-	pF



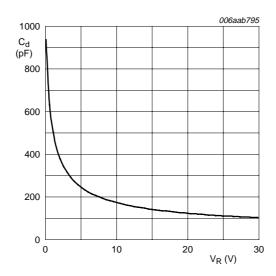
- (1) $T_i = 150 \,^{\circ}\text{C}$
- (2) $T_i = 125 \, ^{\circ}C$
- (3) $T_i = 85 \,^{\circ}C$
- (4) $T_j = 25 \,{}^{\circ}C$
- (5) $T_i = -40 \, ^{\circ}C$

Fig 4. Forward current as a function of forward voltage; typical values



- (1) T_j = 125 °C
- (2) $T_j = 85 \,^{\circ}C$
- (3) $T_j = 25 \,^{\circ}C$
- (4) $T_j = -40 \, ^{\circ}C$

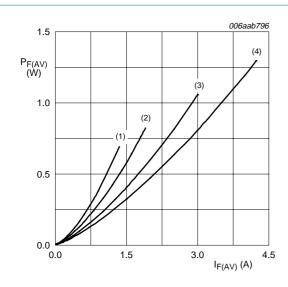
Fig 5. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 6. Diode capacitance as a function of reverse voltage; typical values

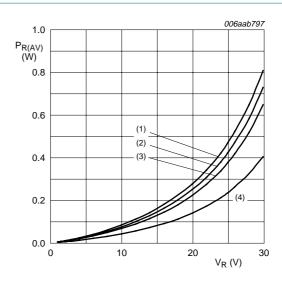
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T_i = 150 °C

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

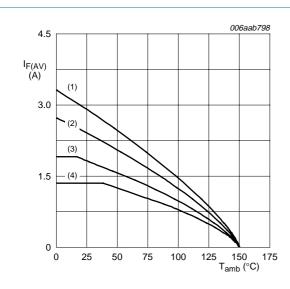
Average forward power dissipation as a Fig 7. function of average forward current; typical values



T_i = 125 °C

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

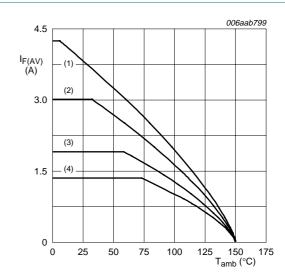
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

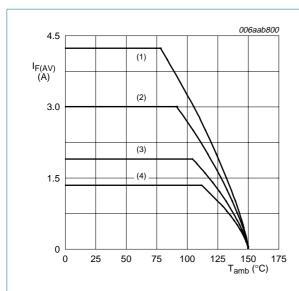
Fig 10. Average forward current as a function of ambient temperature; typical values

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Ceramic PCB, Al₂O₃, standard footprint

T_i = 150 °C

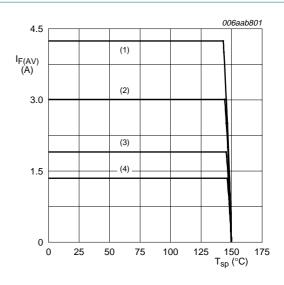
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



T_i = 150 °C

(1) $\delta = 1$; DC

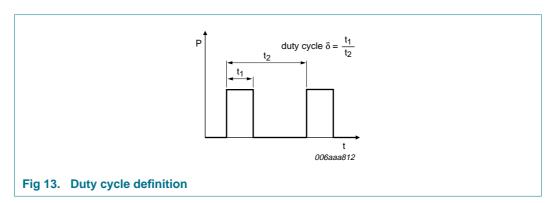
(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

8. Test information

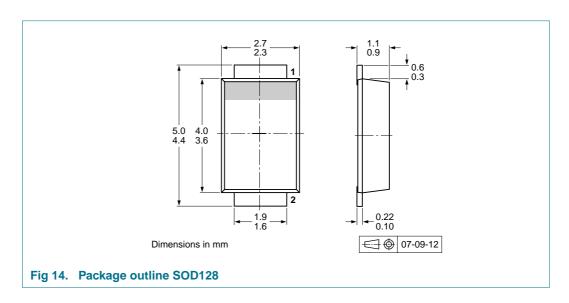


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

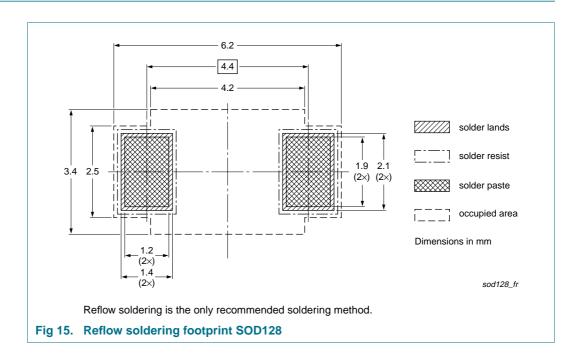
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	number Package Description		Packing quantity
			3000
PMEG3030BEP	SOD128	4 mm pitch, 12 mm tape and reel	-115

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering





12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3030BEP_1	20091027	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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